CLAIM AMENDMENTS:

Please amend the claims as follows:

1. (Currently amended) A semiconductor light emitting device comprising:

a semiconductor lamination portion formed by laminating at least an n-type layer and a p-type layer made of gallium nitride based compound semiconductor so as to form a light emitting portion;

a light transmitting conductive layer formed on a surface of the semiconductor lamination portion;

an upper electrode formed so as to be in contact with an exposed surface of the p-type layer of the semiconductor lamination portion exposed by removing a part of the light transmitting conductive layer, and to be in contact with the light transmitting conductive layer on a periphery of the part removed; and

an electric current blocking portion formed on the exposed surface of the semiconductor lamination portion, the electric current blocking portion preventing electric current from flowing into a part of the semiconductor lamination portion under the upper electrode through the electric current blocking portion,

wherein the upper electrode is adhered to the electric current blocking portion of the surface of the semiconductor lamination portion.

2. (Previously presented) The semiconductor light emitting device according to claim 1, wherein the electric current blocking portion is a recessed portion formed on the exposed surface of the semiconductor lamination portion.

3. (Previously presented) The semiconductor light emitting device according to claim 1, wherein the electric current blocking portion is an oxygen containing layer in which oxygen is contained on the exposed surface of the semiconductor lamination portion.

4. (Previously presented) The semiconductor light emitting device according to claim 2, wherein the recessed portion is formed with a depth of 10 to 50 nm.

5. (Withdrawn) A method for manufacturing a semiconductor light emitting device comprising steps of:

forming a semiconductor lamination portion by laminating gallium nitride based compound semiconductor layers so as to form a light emitting portion including an n-type layer and a p-type layer on a substrate;

forming a light transmitting conductive layer on the semiconductor lamination portion;

exposing a surface of the semiconductor lamination portion by etching a part of the light transmitting conductive layer where an upper electrode is planning to be formed;

forming an electric current blocking means by exposing the exposed surface of the semiconductor lamination portion which is exposed by the etching to oxygen plasma; and

forming an upper electrode so as to adhere to the exposed surface of the semiconductor lamination portion formed as the electric current blocking means and to a vicinity of an opening of the light transmitting conductive layer.

6. (Withdrawn) The method for manufacturing a semiconductor light emitting device according to claim 5, further comprising the steps instead of the steps of exposing to the oxygen plasma and forming the upper electrode:

forming a recessed portion on the exposed surface of the semiconductor lamination portion by a dry etching; and

forming an upper electrode so as to adhere to an exposed surface in the recessed portion and to a vicinity of an opening of the light transmitting conductive layer.

7. (Withdrawn) The method for manufacturing a semiconductor light emitting device according to claim 5, wherein treating by the oxygen plasma is applied with a plasma source power of 200 to 400 W for 5 to 30 minutes.

8. (New) The semiconductor light emitting device according to claim 1, wherein the upper electrode is formed with a lamination structure made of one of:

Ti/Au,

Pd/Au, and

Ni/Au.

9. (New) The semiconductor light emitting device according to claim 1, wherein the p-type layer has a thickness of 0.1 to 1μm.

10. (New) The semiconductor light emitting device according to claim 1, wherein the upper electrode has a thickness of 0.2 to 1 μm.

11. (New) The semiconductor light emitting device according to claim 1, wherein the light transmitting conductive layer is formed with one of:

a ZnO layer,

an ITO layer, and

an alloy layer made by alloying Ni layer and Au previously laminated together.